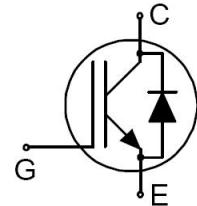


1200V , 15A , Trench-FS IGBT**Features**

- Advanced Trench+FS (Field Stop) IGBT technology
- Low Collector-Emitter Saturation voltage, typical data is 2.1V @ 15A.
- Easy parallel switching capability due to positive Temperature coefficient in Vce.
- Short-Circuit withstand time-10uS
- Fast switching
- High input impedance
- Pb- Free product

**Schematic Diagram****TO-247****Applications**

- Industry Inverter
- Power switch circuit of induction cooker

Electrical characteristics(TJ = 25°C unless otherwise noted)

Symbol	Parameter	Test conditions	Units	Min.	Typ.	Max.
$V_{(BR)CES}$	Collector - Emitter breakdown voltage	$V_{GE} = 0V, I_D = 0.5mA$	V	1200	—	—
$V_{CE(sat)}$	Collector-Emitter Saturation voltage	$V_{GE}=15V, I_C=15A, T_C=25^\circ C$	V	—	2.1	2.5
		$V_{GE}=15V, I_C=15A, T_C=125^\circ C$	V	—	2.35	—
$V_{GE(th)}$	Gate threshold voltage	$V_{GE}= V_{CE}, I_D = 0.4mA$	V	4.0	5.8	6.5
V_F	Diode Forward voltage	$I_C=15A$	V	—	2.1	2.6
I_{GES}	Gate to Emitter Forward Leakage	$V_{GE}=+30V$	nA	—	—	200
I_{GESR}	Gate to Emitter reverse Leakage	$V_{GE}=-30V$		-200	—	—
I_{CES}	Zero gate voltage collector current	$V_{CE} = 1200V$	uA	—	—	100